

Materials List for:

Analysis of Contact Interfaces for Single GaN Nanowire Devices

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Materials

Name	Company	Catalog Number	Comments
REAGENTS and MATERIALS			
Lift-off resist	MicroChem	LOR 5A	Varies according to application
Photoresist	ShIPLEY	1813	Varies according to application
Developer	Rohm and Haas Electronic Materials	MF CD-26	Varies according to application
Photoresist stripper	MicroChem	Nano Remover PG	Varies according to application
Ni source	International Advanced Materials	99.999% purity	
Au source	International Advanced Materials	99.999% purity	
SiO ₂ /Si wafers	Silicon Valley Microelectronics	3-inch <100> N/As 0.001-0.005 ohm-cm, 200 nm thermal oxide	
Carbon tape	SPI Supplies	5072, 8 mm wide	
Solvents are standard semiconductor or research grade. Vendor is not important for the experimental outcome.			
Reactive ion etch gases and thermal annealing gases are high purity grade. Vendor is not important for the experimental outcome.			
EQUIPMENT			
Ultrasonic cleaner	Cole-Palmer	EW-08849-00	Low power
Micropipette	Rainin	PR-200	Metered, disposal tips
Reactive ion etcher	SemiGroup	RIE 1000 TP	Other vendors also used with different process parameters
Mask aligner	Karl Suss	MJB3	Other vendors also used with different process parameters
UV ozone cleaner	Jelight	Model 42	Other vendors also used with different process parameters
E-beam evaporator	CVC	SC-6000	Other vendors also used with different process parameters
* Manufacturers and product names are given solely for completeness. These specific citations neither constitute an endorsement of the product by NIST nor imply that similar products from other companies would be less suitable.			